

NTJD4105C

Small Signal MOSFET

20 V / -8.0 V, Complementary,
+0.63 A / -0.775 A, SC-88

Features

- Complementary N and P Channel Device
- Leading -8.0 V Trench for Low $R_{DS(on)}$ Performance
- ESD Protected Gate – ESD Rating: Class 1
- SC-88 Package for Small Footprint (2 x 2 mm)
- Pb-Free Packages are Available

Applications

- DC-DC Conversion
- Load/Power Switching
- Single or Dual Cell Li-Ion Battery Supplied Devices
- Cell Phones, MP3s, Digital Cameras, PDAs

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage		N-Ch	V_{DSS}	20	V
		P-Ch		-8.0	
Gate-to-Source Voltage		N-Ch	V_{GS}	± 12	V
		P-Ch		± 8.0	
Continuous Drain Current – Steady State (Based on $R_{\theta JA}$)	N-Ch	$T_A = 25^{\circ}\text{C}$	I_D	0.63	A
		$T_A = 85^{\circ}\text{C}$		0.46	
	P-Ch	$T_A = 25^{\circ}\text{C}$		-0.775	
		$T_A = 85^{\circ}\text{C}$		-0.558	
Continuous Drain Current – Steady State (Based on $R_{\theta JL}$)	N-Ch	$T_A = 25^{\circ}\text{C}$		0.91	
		$T_A = 85^{\circ}\text{C}$		0.65	
	P-Ch	$T_A = 25^{\circ}\text{C}$		-1.1	
		$T_A = 85^{\circ}\text{C}$		-0.8	
Pulsed Drain Current		$tp \leq 10 \mu s$	I_{DM}	± 1.2	A
Power Dissipation – Steady State (Based on $R_{\theta JA}$)		$T_A = 25^{\circ}\text{C}$	P_D	0.27	W
		$T_A = 85^{\circ}\text{C}$		0.14	
Power Dissipation – Steady State (Based on $R_{\theta JL}$)		$T_A = 25^{\circ}\text{C}$		0.55	
		$T_A = 85^{\circ}\text{C}$		0.29	
Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode)		N-Ch	I_S	0.63	A
		P-Ch		-0.775	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS (Note 1)

Junction-to-Ambient – Steady State	Typ	$R_{\theta JA}$	400	$^\circ\text{C/W}$
	Max		460	
Junction-to-Lead (Drain) – Steady State	Typ	$R_{\theta JL}$	194	
	Max		226	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 oz Cu area = 0.9523 in sq.

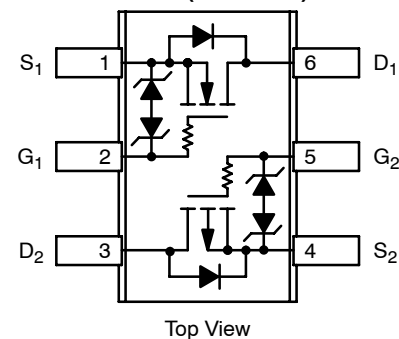


ON Semiconductor®

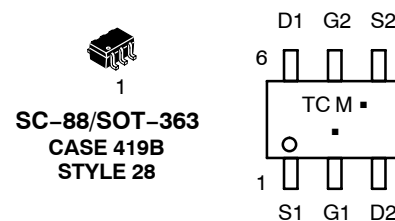
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max
N-Ch 20 V	0.29 Ω @ 4.5 V	0.63 A
	0.36 Ω @ 2.5 V	
P-Ch -8.0 V	0.22 Ω @ -4.5 V	-0.775 A
	0.32 Ω @ -2.5 V	
	0.51 Ω @ -1.8 V	

SOT-363
SC-88 (6-LEADS)



MARKING DIAGRAM & PIN ASSIGNMENT



SC-88/SOT-363
CASE 419B
STYLE 28

TC = Device Code
M = Date Code
• = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

NTJD4105C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Units
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	N	V _{GS} = 0 V	I _D = 250 μA	20	27	V
		P		I _D = -250 μA	-8.0	-10.5	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} / T _J	N			22		mV/°C
		P			-6.0		
Zero Gate Voltage Drain Current	I _{DSS}	N	V _{GS} = 0 V, V _{DS} = 16 V	T _J = 25 °C		1.0	μA
		P	V _{GS} = 0 V, V _{DS} = -6.4 V			1.0	
Gate-to-Source Leakage Current	I _{GSS}	N	V _{DS} = 0 V	V _{GS} = ±12 V		10	μA
		P		V _{GS} = ±8.0		10	

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	N	V _{GS} = V _{DS}	I _D = 250 μA	0.6	0.92	1.5	V
		P		I _D = -250 μA	-0.45	-0.83	-1.0	
Gate Threshold Temperature Coefficient	V _{GS(TH)} / T _J	N				-2.1		-mV/ °C
		P				2.2		
Drain-to-Source On Resistance	R _{DS(on)}	N	V _{GS} = 4.5 V, I _D = 0.63 A			0.29	0.375	Ω
		P	V _{GS} = -4.5 V, I _D = -0.57 A			0.22	0.30	
		N	V _{GS} = 2.5 V, I _D = 0.40 A			0.36	0.445	
		P	V _{GS} = -2.5 V, I _D = -0.48 A			0.32	0.46	
		P	V _{GS} = -1.8 V, I _D = -0.20 A			0.51	0.90	
Forward Transconductance	g _{FS}	N	V _{DS} = 4.0 V, I _D = 0.63 A			2.0		S
		P	V _{DS} = -4.0 V, I _D = -0.57 A			2.0		

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	N	f = 1 MHz, V _{GS} = 0 V	V _{DS} = 20 V		33	46	pF
		P		V _{DS} = -8.0 V		160	225	
Output Capacitance	C _{OSS}	N		V _{DS} = 20 V		13	22	
		P		V _{DS} = -8.0 V		38	55	
Reverse Transfer Capacitance	C _{RSS}	N		V _{DS} = 20 V		2.8	5.0	
		P		V _{DS} = -8.0 V		28	40	
Total Gate Charge	Q _{G(TOT)}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.7 A		1.3	3.0	nC
		P		V _{GS} = -4.5 V, V _{DS} = -5.0 V, I _D = -0.6 A		2.2	4.0	
Threshold Gate Charge	Q _{G(TH)}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.7 A		0.1		
		P		V _{GS} = -4.5 V, V _{DS} = -5.0 V, I _D = -0.6 A		0.1		
Gate-to-Source Charge	Q _{GS}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.7 A		0.2		
		P		V _{GS} = -4.5 V, V _{DS} = -5.0 V, I _D = -0.6 A		0.5		
Gate-to-Drain Charge	Q _{GD}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.7 A		0.4		
		P		V _{GS} = -4.5 V, V _{DS} = -5.0 V, I _D = -0.6 A		0.5		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	N	V _{GS} = 4.5 V, V _{DD} = 10 V, I _D = 0.5 A, R _G = 20 Ω		0.083		μs
Rise Time	t _r				0.227		
Turn-Off Delay Time	t _{d(OFF)}				0.786		
Fall Time	t _f				0.506		
Turn-On Delay Time	t _{d(ON)}	P	V _{GS} = -4.5 V, V _{DD} = -4.0 V, I _D = -0.5 A, R _G = 8.0 Ω		0.013		
Rise Time	t _r				0.023		
Turn-Off Delay Time	t _{d(OFF)}				0.050		
Fall Time	t _f				0.036		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	N	V _{GS} = 0 V, T _J = 25°C	I _S = 0.23 A		0.76	1.1	V
		P		I _S = -0.23 A		0.76	1.1	
		N	V _{GS} = 0 V, T _J = 125°C	I _S = 0.23 A		0.63		
		P		I _S = -0.23 A		0.63		
Reverse Recovery Time	t _{RR}	N	V _{GS} = 0 V, dI _S /dt = 90 A/μs	I _S = 0.23 A		0.410		μs
		P		I _S = -0.23 A		0.078		

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL N-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

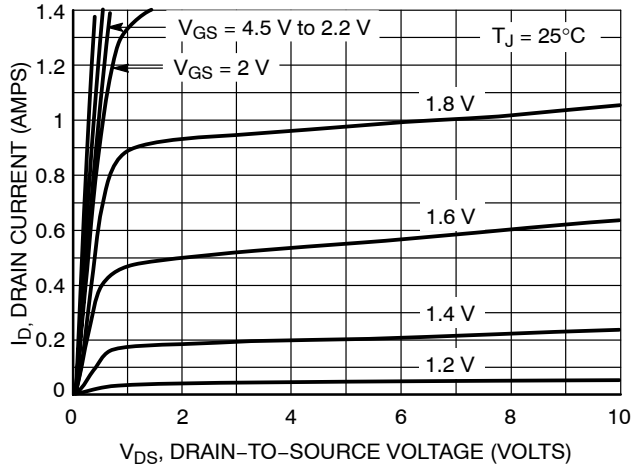


Figure 1. On-Region Characteristics

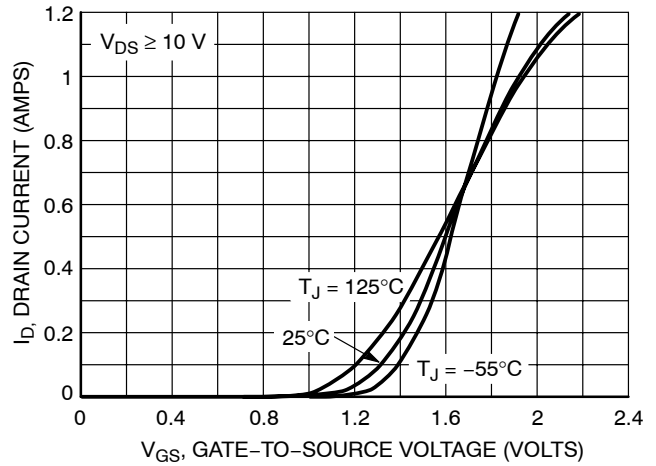


Figure 2. Transfer Characteristics

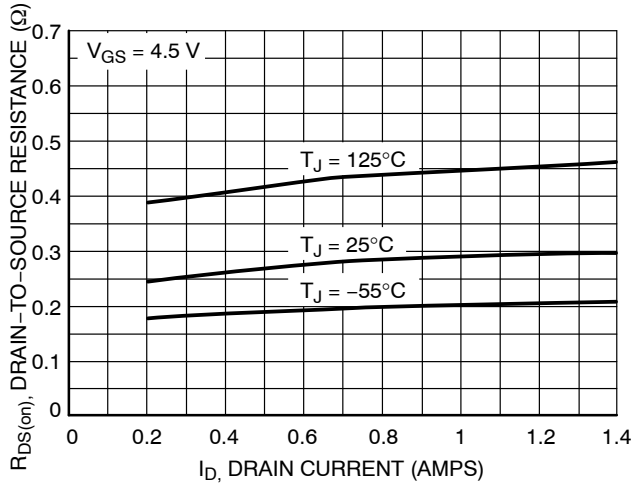


Figure 3. On-Resistance vs. Drain Current and Temperature

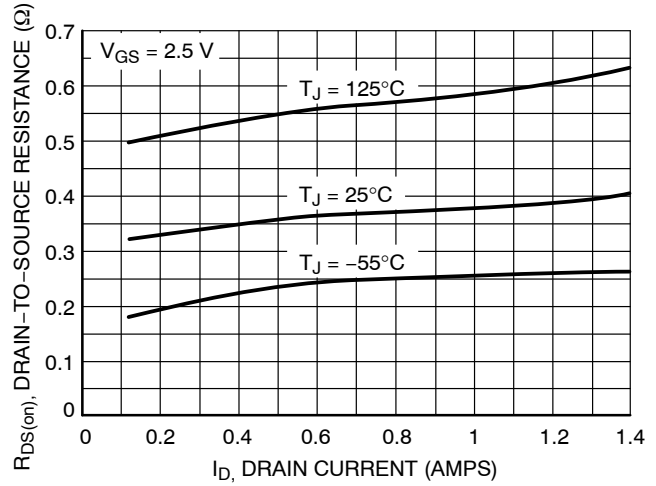


Figure 4. On-Resistance vs. Drain Current and Temperature

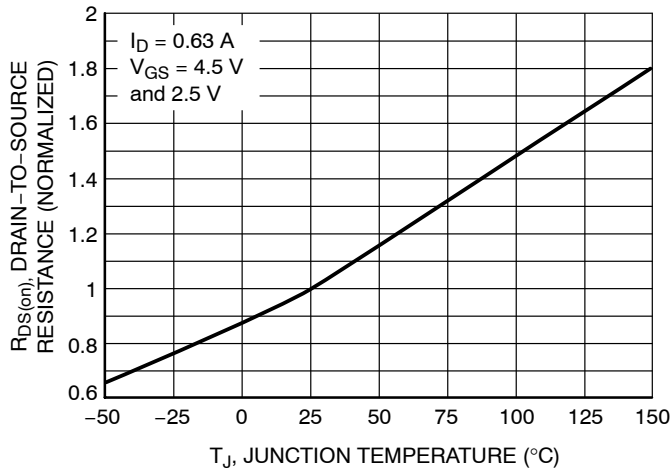


Figure 5. On-Resistance Variation with Temperature

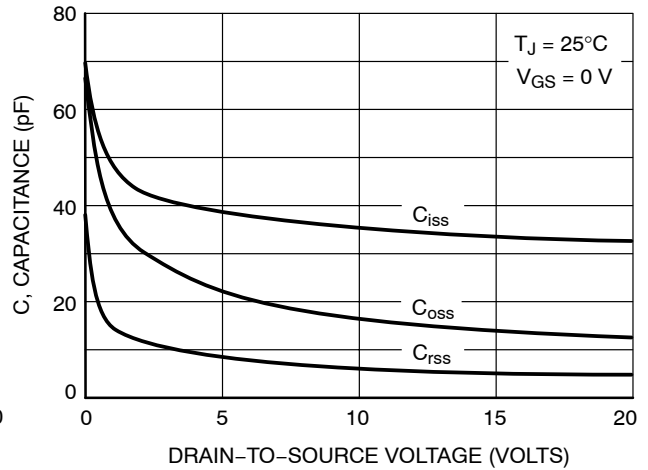


Figure 6. Capacitance Variation

TYPICAL N-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

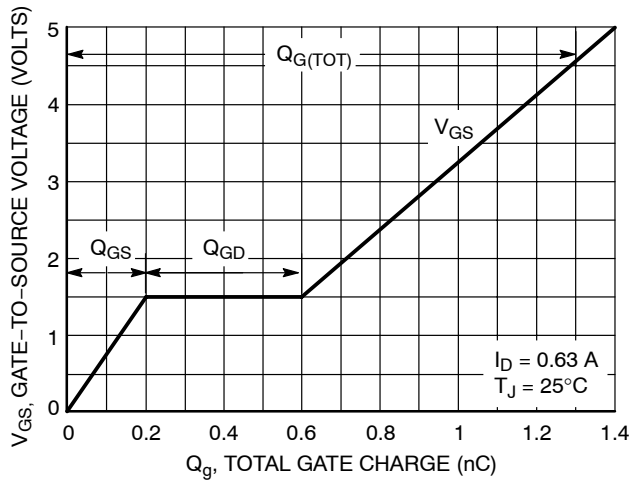


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

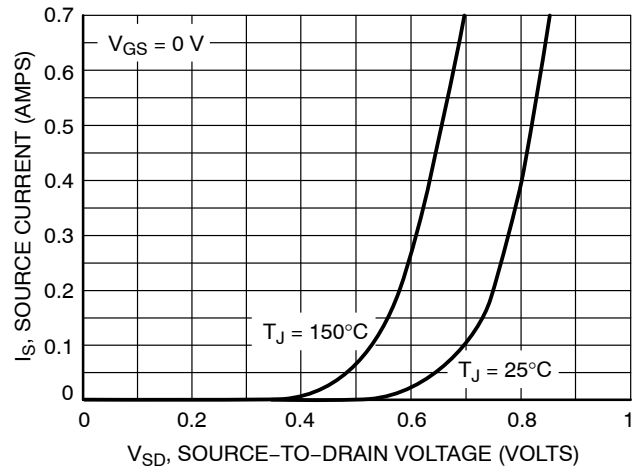


Figure 8. Diode Forward Voltage vs. Current

TYPICAL P-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

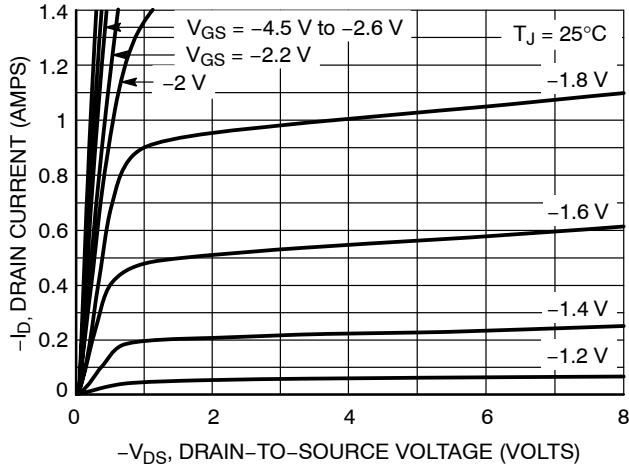


Figure 9. On-Region Characteristics

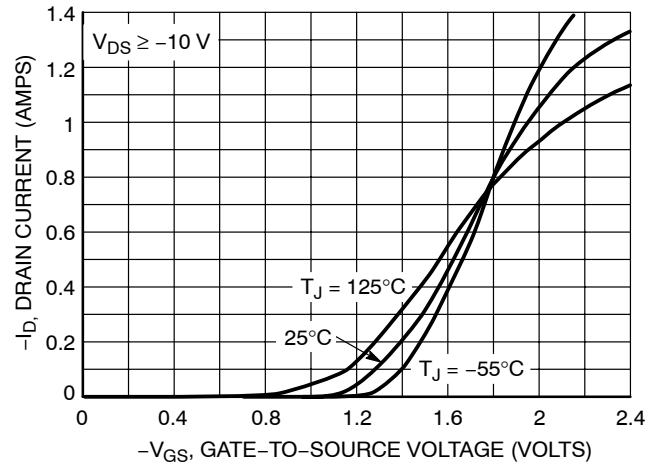


Figure 10. Transfer Characteristics

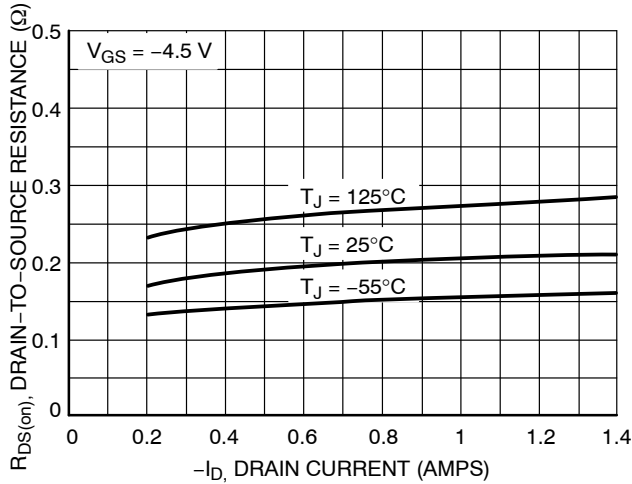


Figure 11. On-Resistance vs. Drain Current and Temperature

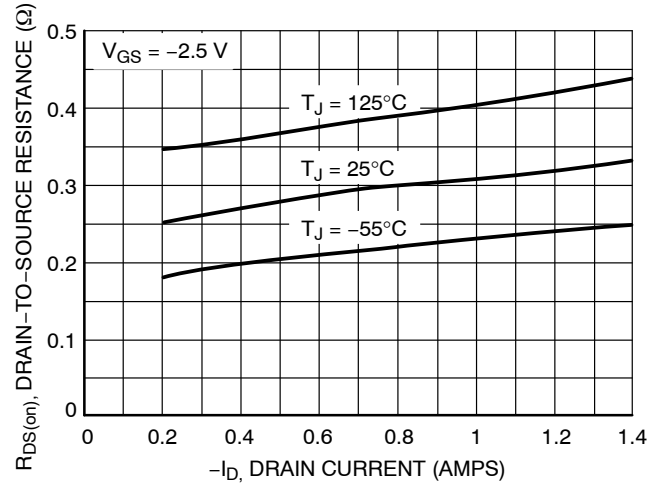


Figure 12. On-Resistance vs. Drain Current and Temperature

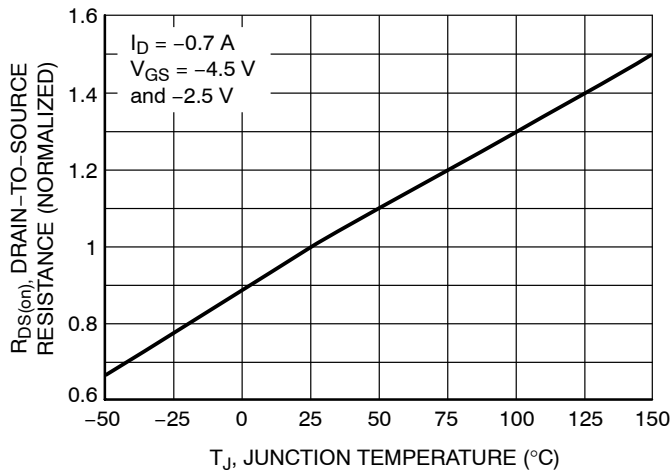


Figure 13. On-Resistance Variation with Temperature

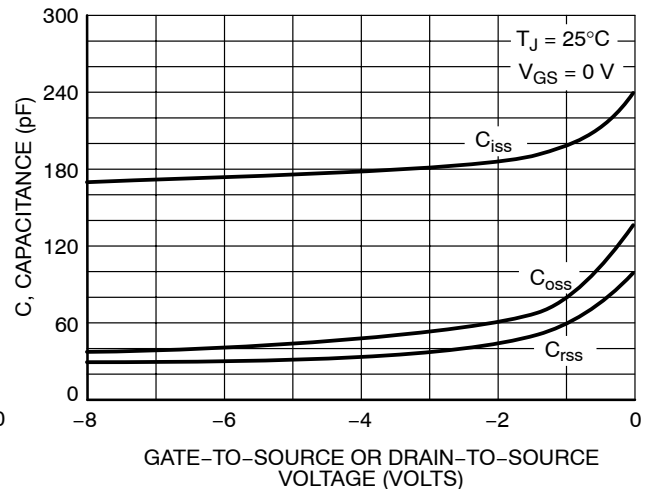


Figure 14. Capacitance Variation

TYPICAL P-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

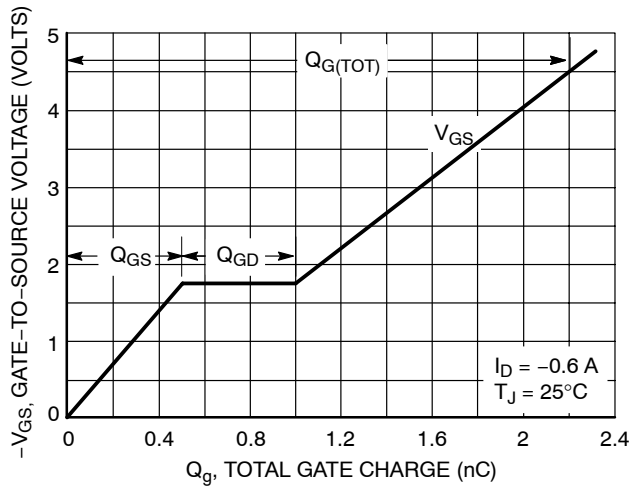


Figure 15. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

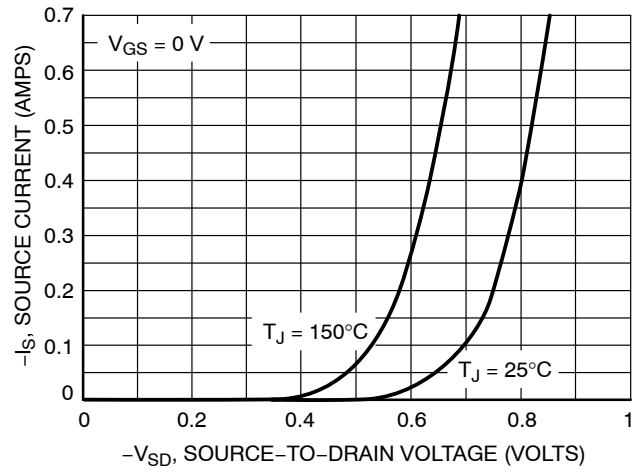


Figure 16. Diode Forward Voltage vs. Current

NTJD4105C

ORDERING INFORMATION

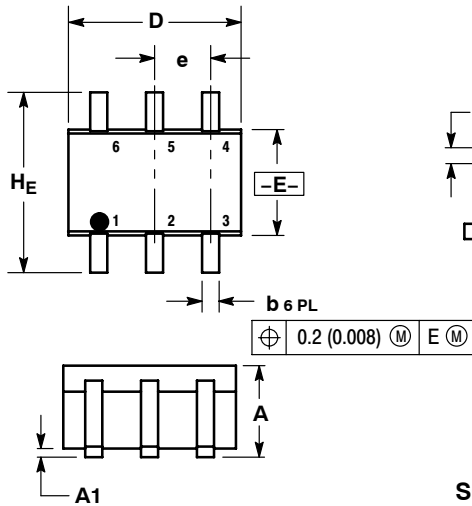
Device	Package	Shipping [†]
NTJD4105CT1	SOT-363	3000 / Tape & Reel
NTJD4105CT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NTJD4105CT2	SOT-363	3000 / Tape & Reel
NTJD4105CT2G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NTJD4105CT4	SOT-363	10,000 / Tape & Reel
NTJD4105CT4G	SOT-363 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTJD4105C

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE W



NOTES:

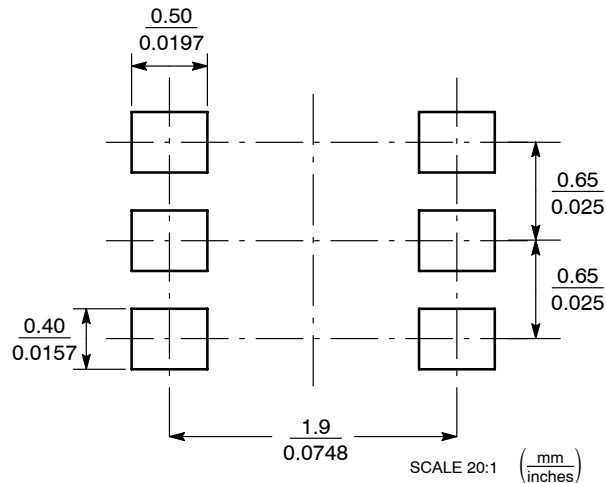
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 26:

1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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